74LCX16245

LOW VOLTAGE CMOS 16-BIT BUS TRANSCEIVER WITH 5V TOLERANT INPUTS AND OUTPUT (3-STATE)

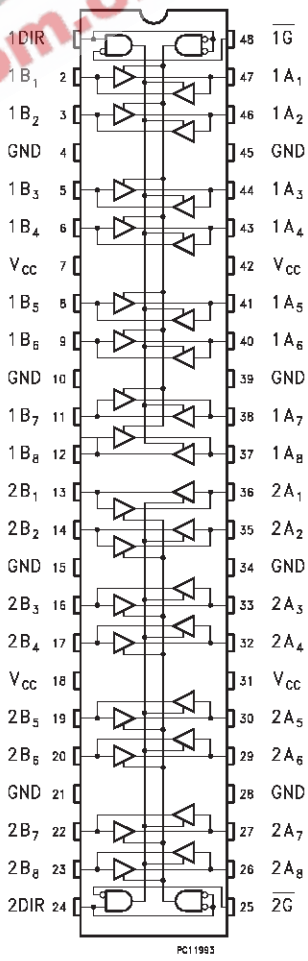
- 5V TOLERANT INPUTS AND OUTPUTS
- HIGH SPEED :
  t_{PD} = 4.5 ns (MAX.) at V_{CC} = 3V
- POWER DOWN PROTECTION ON INPUTS AND OUTPUTS
- SYMMETRICAL OUTPUT IMPEDANCE:
  $|I_{OH}| = I_{OL}$ = 24mA (MIN) at V_{CC} = 3V
- PCI BUS LEVELS GUARANTEED AT 24 mA
- BALANCED PROPAGATION DELAYS:
  $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE:
  V_{CC}(OPR) = 2.0V to 3.6V (1.5V Data Retention)
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 16245
- LATCH-UP PERFORMANCE EXCEEDS 500mA (JESD 17)
- ESD PERFORMANCE:
  HBM > 2000V (MIL STD 883 method 3015);
  MM > 200V

TSSOP

ORDER CODES

PACKAGE	TUBE	T & R
TSSOP		74LCX16245TTR

PIN CONNECTION



DESCRIPTION

The 74LCX16245 is a low voltage CMOS 16 BIT BUS TRANSCEIVER (3-STATE) fabricated with sub-micron silicon gate and double-layer metal wiring C^2MOS technology. It is ideal for low power and high speed 3.3V applications; it can be interfaced to 5V signal environment for both inputs and outputs.

This IC is intended for two-way asynchronous communication between data buses; the direction of data transmission is determined by DIR input.

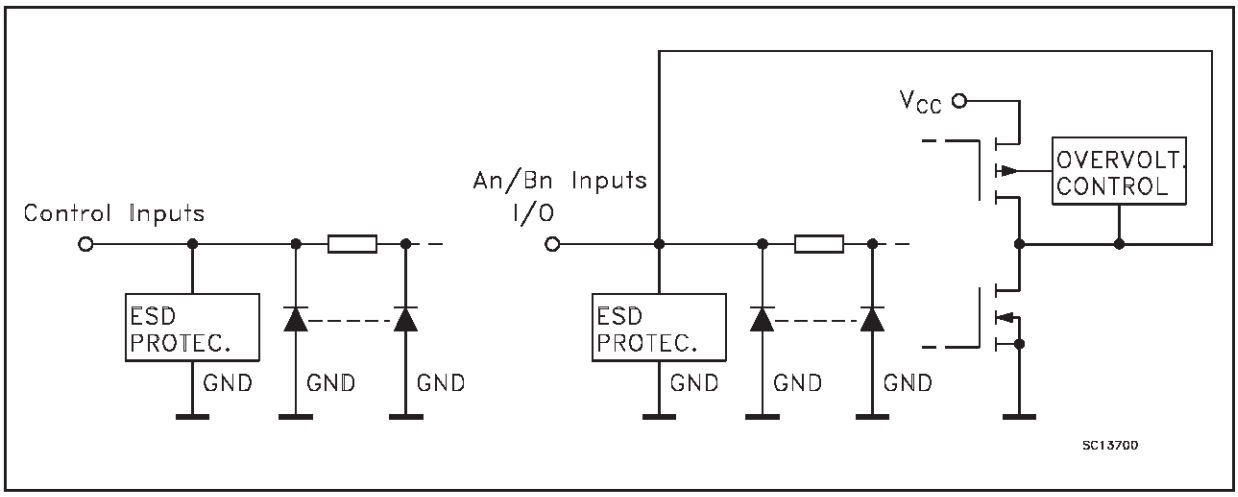
The two enable inputs $n\overline{G}$ can be used to disable the device so that the buses are effectively isolated.

It has same speed performance at 3.3V than 5V AC/ACT family, combined with a lower power consumption.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

All floating bus terminals during High Z State must be held HIGH or LOW.

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

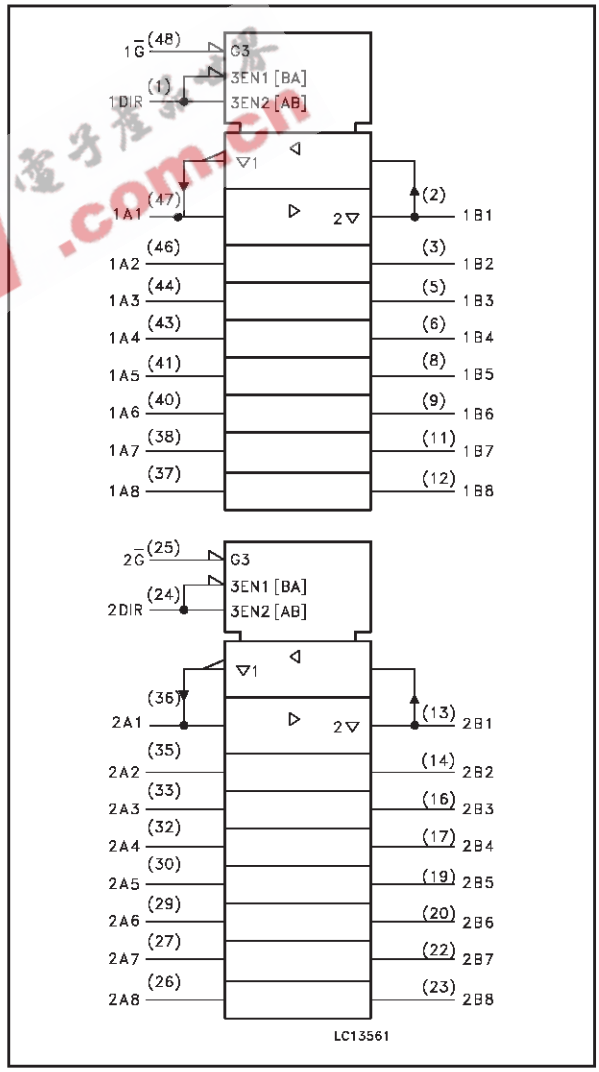
PIN No	SYMBOL	NAME AND FUNCTION
1	1DIR	Directional Control
2, 3, 5, 6, 8, 9, 11, 12	1B1 to 1B8	Data Inputs/Outputs
13, 14, 16, 17, 19, 20, 22, 23	2B1 to 2B8	Data Inputs/Outputs
24	2DIR	Directional Control
25	$\overline{2G}$	Output Enable Input
36, 35, 33, 32, 30, 29, 27, 26	2A1 to 2A8	Data Inputs/Outputs
47, 46, 44, 43, 41, 40, 38, 38	1A1 to 1A8	Data Inputs/Outputs
48	$\overline{1G}$	Output Enable Input
4, 10, 15, 21, 28, 34, 39, 45	GND	Ground (0V)
7, 18, 31, 42	V_{CC}	Positive Supply Voltage

TRUTH TABLE

INPUTS		FUNCTION		OUTPUT
$\overline{G}$	DIR	A BUS	B BUS	Yn
L	L	OUTPUT	INPUT	A = B
L	H	INPUT	OUTPUT	B = A
H	X	Z	Z	Z

X : Don't Care
Z : High Impedance

IEC LOGIC SYMBOLS



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7.0	V
V_I	DC Input Voltage (DIR, $\overline{G}$)	-0.5 to +7.0	V
$V_{I/O}$	Bus I/O Voltage (OFF State)	-0.5 to +7.0	V
$V_{I/O}$	Bus I/O Voltage (High or Low State) (note 1)	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	- 50	mA
I_{OK}	DC Output Diode Current (note 2)	- 50	mA
I_O	DC Output Current	± 50	mA
I_{CC}	DC Supply Current per Supply Pin	± 100	mA
I_{GND}	DC Ground Current per Supply Pin	± 100	mA
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied
1) I_O absolute maximum rating must be observed
2) V_O < GND

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage (note 1)	2.0 to 3.6	V
V_I	Input Voltage	0 to 5.5	V
V_O	Output Voltage (OFF State)	0 to 5.5	V
V_O	Output Voltage (High or Low State)	0 to V_{CC}	V
I_{OH}, I_{OL}	High or Low Level Output Current (V_{CC} = 3.0 to 3.6V)	± 24	mA
I_{OH}, I_{OL}	High or Low Level Output Current (V_{CC} = 2.7V)	± 12	mA
T_{op}	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 2)	0 to 10	ns/V

1) Truth Table guaranteed: 1.5V to 3.6V
2) V_{IN} from 0.8V to 2V at V_{CC} = 3.0V

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value				Unit
		V_{CC} (V)		-40 to 85 °C		-55 to 125 °C		
				Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	2.7 to 3.6		2.0		2.0		V
V_{IL}	Low Level Input Voltage				0.8		0.8	V
V_{OH}	High Level Output Voltage	2.7 to 3.6	I_O=-100 µA	V_{CC}-0.2		V_{CC}-0.2		V
		2.7	I_O=-12 mA	2.2		2.2		
		3.0	I_O=-18 mA	2.4		2.4		
			I_O=-24 mA	2.2		2.2		
V_{OL}	Low Level Output Voltage	2.7 to 3.6	I_O=100 µA		0.2		0.2	V
		2.7	I_O=12 mA		0.4		0.4	
		3.0	I_O=16 mA		0.4		0.4	
			I_O=24 mA		0.55		0.55	
I_I	Input Leakage Current	2.7 to 3.6	V_I = 0 to 5.5V		± 5		± 5	µA
I_{off}	Power Off Leakage Current	0	V_I or V_O = 5.5V		10		10	µA
I_{OZ}	High Impedance Output Leakage Current	2.7 to 3.6	V_I = V_{IH} or V_{IL} V_O = 0 to V_{CC}		± 5		± 5	µA
I_{CC}	Quiescent Supply Current	2.7 to 3.6	V_I = V_{CC} or GND		20		20	µA
			V_I or V_O= 3.6 to 5.5V		± 20		± 20	
ΔI_{CC}	I_{CC} incr. per Input	2.7 to 3.6	V_{IH} = V_{CC} - 0.6V		500		500	µA

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Condition		Value			Unit
		V_{CC} (V)		T_A = 25 °C			
				Min.	Typ.	Max.	
V_{OLP}	Dynamic Low Level Quiet Output (note 1)	3.3	C_L = 50pF V_{IL} = 0V, V_{IH} = 3.3V		0.8		V
V_{OLV}					-0.8		

1) Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH to LOW or LOW to HIGH. The remaining output is measured in the LOW state.

AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Condition				Value				Unit
		V_{CC} (V)	C_L (pF)	R_L (Ω)	$t_s = t_r$ (ns)	-40 to 85 °C		-55 to 125 °C		
						Min.	Max.	Min.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time	2.7	50	500	2.5	1.5	5.2	1.5	5.2	ns
		3.0 to 3.6				1.5	4.5	1.5	4.5	
t_{PZL} t_{PZH}	Output Enable Time	2.7	50	500	2.5	1.5	7.2	1.5	7.2	ns
		3.0 to 3.6				1.5	6.5	1.5	6.5	
t_{PLZ} t_{PHZ}	Output Disable Time	2.7	50	500	2.5	1.5	6.9	1.5	6.9	ns
		3.0 to 3.6				1.5	6.4	1.5	6.4	
t_{OSLH} t_{OSHL}	Output To Output Skew Time (note1, 2)	3.0 to 3.6	50	500	2.5		1.0		1.0	ns

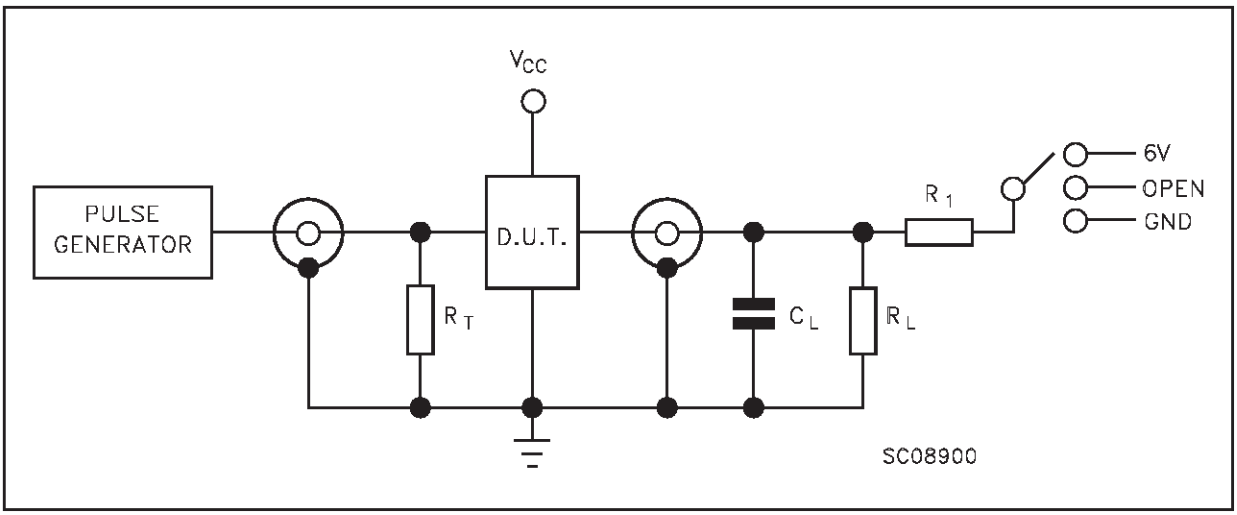
1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW ($t_{OSLH} = |t_{PLHm} - t_{PLHn}|$, $t_{OSHL} = |t_{PHLm} - t_{PHLn}|$)
2) Parameter guaranteed by design

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value			Unit
		V_{CC} (V)		T_A = 25 °C			
				Min.	Typ.	Max.	
C_{IN}	Input Capacitance	3.3	V_{IN} = 0 to V_{CC}		7		pF
C_{OUT}	Output Capacitance	3.3	V_{IN} = 0 to V_{CC}		8		pF
C_{PD}	Power Dissipation Capacitance (note 1)	3.3	f_{IN} = 10MHz V_{IN} = 0 or V_{CC}		20		pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/16$ (per circuit)

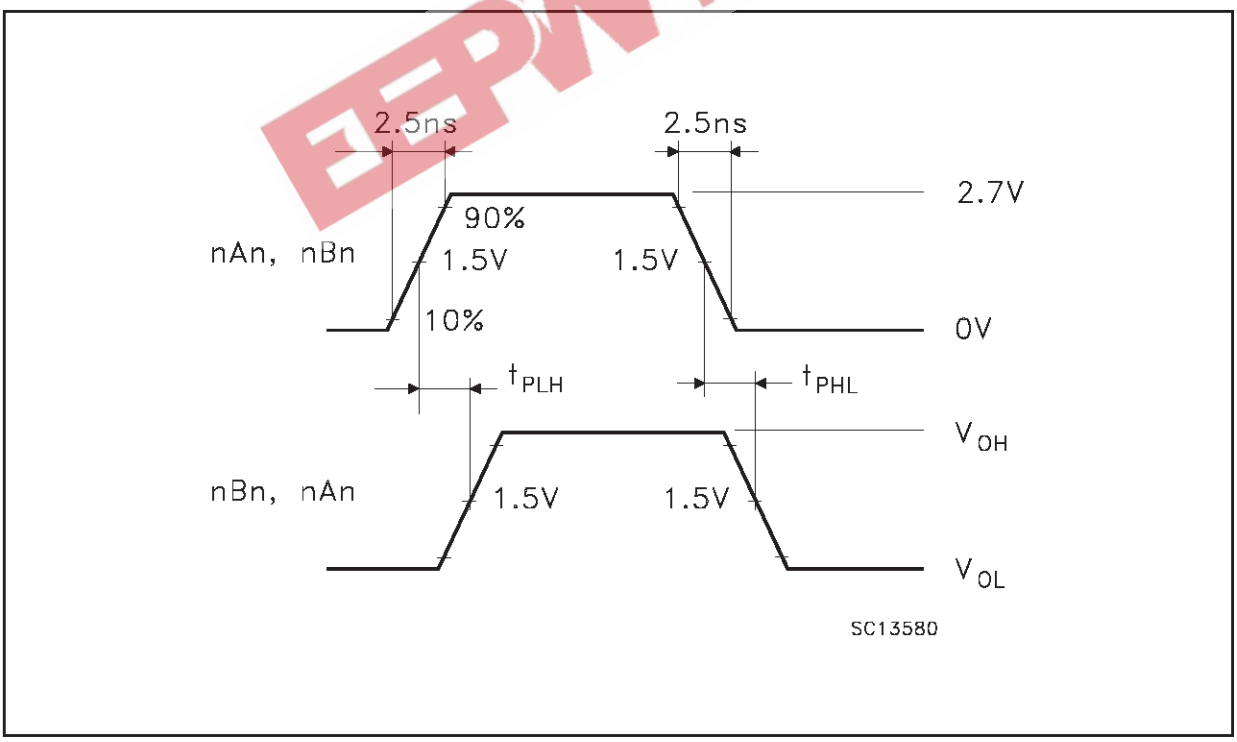
TEST CIRCUIT



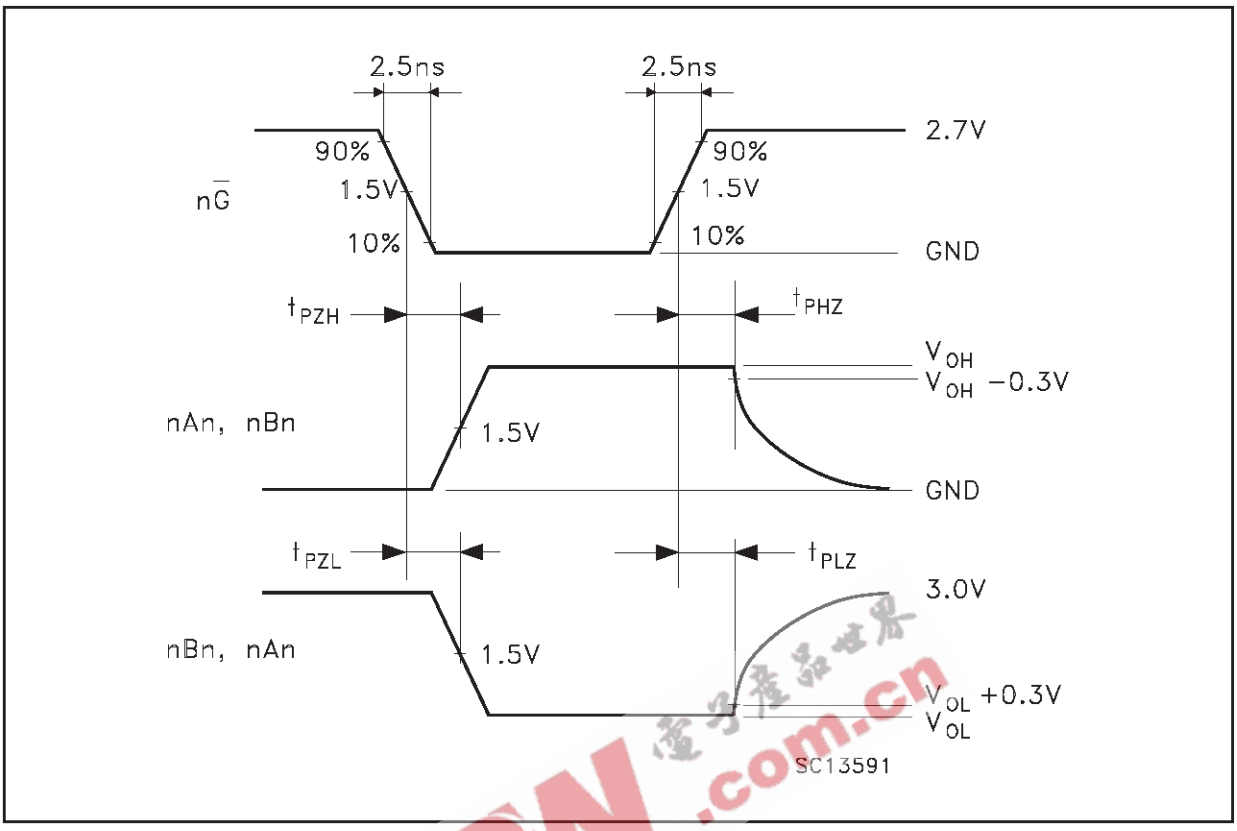
TEST	SWITCH
t_{PLH}, t_{PHL}	Open
t_{PZL}, t_{PLZ}	6V
t_{PZH}, t_{PHZ}	GND

C_L = 50 pF or equivalent (includes jig and probe capacitance)
R_L = R1 = 500Ω or equivalent
R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM 1 : PROPAGATION DELAYS (f=1MHz; 50% duty cycle)



WAVEFORM 2 : OUTPUT ENABLE AND DISABLE TIME (f=1MHz; 50% duty cycle)



TSSOP48 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.1			0.043
A1	0.05		0.15	0.002		0.006
A2		0.9			0.035	
b	0.17		0.27	0.0067		0.011
c	0.09		0.20	0.0035		0.0079
D	12.4		12.6	0.408		0.496
E	7.95		8.25	0.313		0.325
E1	6.0		6.2	0.236		0.244
e		0.5 BSC			0.0197 BSC	
K	0°		8°	0°		8°
L	0.50		0.75	0.020		0.030